APPENDIX B

1. (Twice amended) A method for making a [thin film] transistor containing a gate dielectric structure, comprising:

providing a [substrate for the] gate [dielectric structure] conductor;

providing a channel; and

providing, between the gate conductor and the channel, an oxide layer of the gate dielectric structure [on the substrate] by an in-situ steam generation process.

2. (Cancelled)

3. (Amended) The method of claim 1, wherein the transistor is a thin film transistor [is a floating gate transistor or a SONOS transistor].

4. (Cancelled)

5. (Amended) The method of claim [1] 3, wherein the in-situ steam generation process is performed at a temperature ranging from about 600 to about 900 degrees Celsius.

8. (Amended) The method of claim [1] 28, further including annealing the oxide layer in a nitric oxide atmosphere.

9. (Twice amended) A method for making a [semiconductor] SONOS device, comprising:

providing a [substrate] channel region; [and

providing a gate dielectric structure by:]

providing a first oxide layer on the [substrate] channel region by an in-situ steam generation process;

providing a nitride layer on the first oxide layer; and

providing a second oxide layer on the nitride layer.

10. (Cancelled)

11. (Cancelled)

16. (Cancelled)

17. (Cancelled)

18. (Cancelled)

19. (Cancelled)

20. (Amended) The method of claim [16] 27, further including annealing the oxide layer in a nitric oxide atmosphere.

21. (Amended) A method for making a gate dielectric structure for a [thin film transistor or a] SONOS device, comprising.

providing [a substrate] silicon;

providing an oxide layer of a gate dielectric structure on the silicon by in-situ steam generation, the oxide layer having a thickness of about 10 to about 200 angstroms; and

annealing the oxide layer in a nitric oxide atmosphere.

22. (Amended) A method for making a gate dielectric structure for a thin film transistor or a SONOS device, comprising[.]:

providing a [substrate] gate conductor;

providing a channel region; and

providing, between the gate conductor and the channel region, an oxide layer of a gate dielectric structure [on the substrate] by an in-situ steam generation process

performed at a temperature ranging from about 600 to about 1050 degrees Celsius, a pressure ranging from about 100 millitorr to about 760 torr, and for a time sufficient to deposit an oxide thickness of about 10 to about 200 angstroms[; and

annealing the oxide layer in a nitric oxide atmosphere].

23. (Amended) A thin film transistor containing a gate dielectric structure made by [the] a method comprising:

providing a [substrate for a] gate conductor [dielectric structure];

providing a channel region; and

providing, between the gate conductor and the channel region, an oxide layer of the gate dielectric structure on the [substrate] channel region by an in-situ steam generation process.

24. (Twice amended) A SONOS semiconductor device made by [the] a method comprising:

providing a [substrate] channel region; [and]

[providing a gate dielectric structure by:]

providing a first oxide layer on the [substrate] channel region by an in-situ steam generation process;

providing a nitride layer on the first oxide layer; and

providing a second oxide layer on the nitride layer.

25. (Amended) An integrated circuit containing a thin film transistor with a gate dielectric structure made by [the] a method comprising:

providing a [substrate for the] gate [dielectric structure] conductor;

providing a channel; and

providing; between the gate conductor and the channel, an oxide layer of the gate dielectric structure [on the substrate] by an in-situ steam generation process.

26. (Twice amended) An integrated circuit containing a SONOS semiconductor device made by [the] a method comprising:

providing a [substrate] silicon wafer or silicon layer; [and

providing a gate dielectric structure by:]

providing a first oxide layer on the [substrate] silicon wafer or silicon layer by an in-situ steam generation process;

providing a nitride layer on the first oxide layer; and

providing a second oxide layer on the nitride layer.

27. (New)

28. (New)

29. (New)

30. (New)

31. (New)

32. (New)

33. (New)

34. (New)